

Supporting Information

**Improved Power Conversion Efficiency of Perovskite Solar Cells using Highly Conductive WO<sub>x</sub> doped PEDOT:PSS**

Anil Kanwat, V., Sandhya Rani, Jin Jang\*

Advanced Display Research Center, Department of Information Display, Kyung Hee University, Hoegi-dong, Dongdaemun-gu, Seoul 130-701, South Korea

Email: [jjang@khu.ac.kr](mailto:jjang@khu.ac.kr)

**Table S1.** Summary of PEDOT:PSS treated thin films in the literature.

Ref. #	Solvent	Sheet Resistance (/sq)	Transmittance (%) @ 550 nm	Conductivity (S/cm)	Treatment type
1	DMSO		80	389	Doping
1	EG	450	90	634	Doping
1	DMSO		85	700	Post treatment
1	EG	65	75	1418	Post treatment
2	H <sub>2</sub> SO <sub>4</sub>	67	87	3065	Post treatment
3	H <sub>3</sub> PO <sub>4</sub>	120	80	1460	Post treatment
4	H <sub>2</sub> SO <sub>4</sub>	45	90	4300	Post treatment
This work	EG	25	90	3000	Post treatment
	EG	35	95	1920	Post treatment

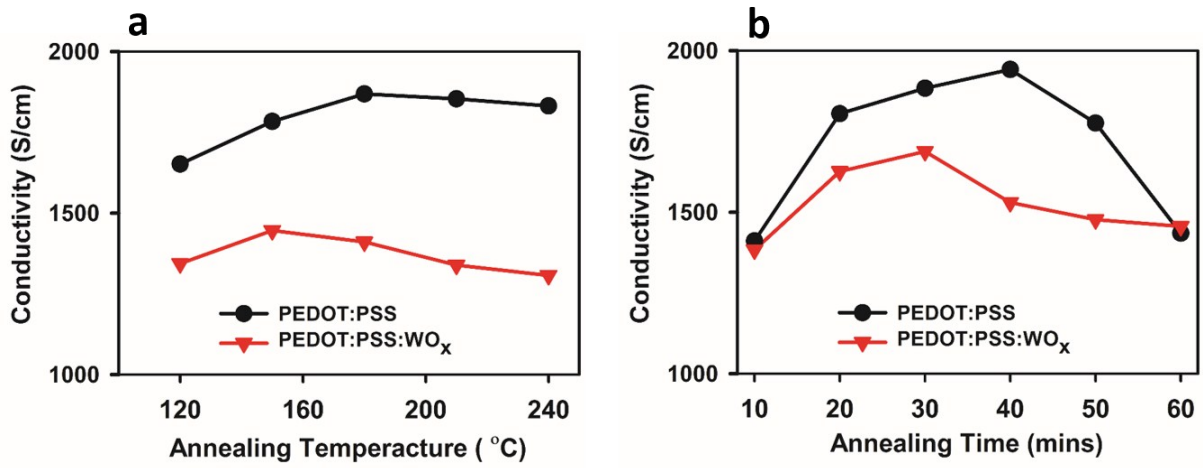


Figure S1. Effect of EG treatment on conductivity of single layered PEDOT:PSS (50nm thick) and PEDOT:PSS:WO<sub>x</sub> (40 nm thick) with (a) annealing temperature (a) and annealing time.

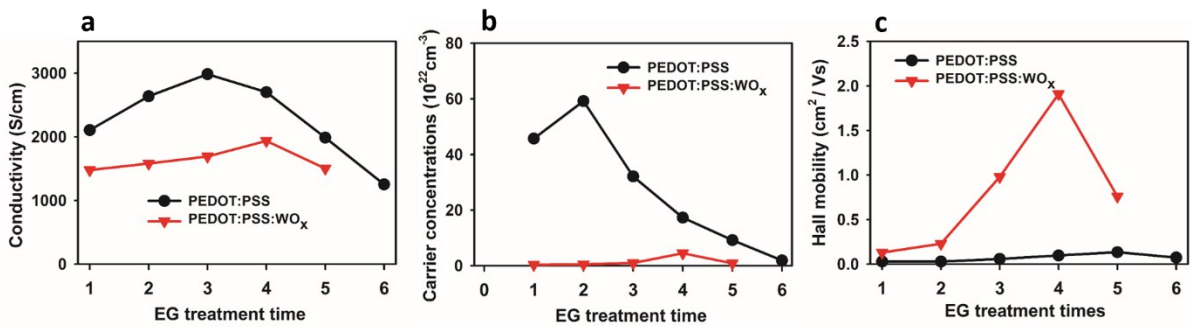


Figure S2. (a) Conductivity, (b) carrier concentrations, and (c) mobility of multiple EG treated on multiple layered of PEDOT:PSS/PEDOT:PSS:WO<sub>x</sub> thin films measured by Hall effect.

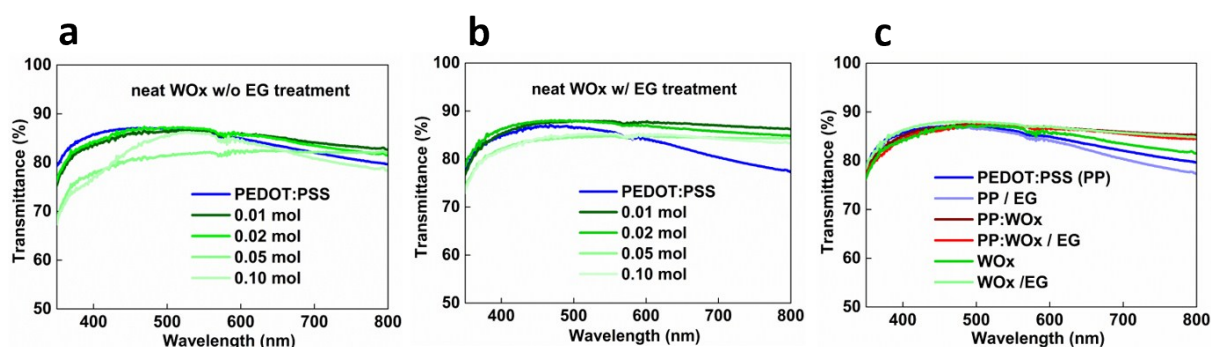


Figure S3. Transmittance plots of (a) neat sol-gel processed  $\text{WO}_x$  thin films, (b) neat sol-gel processed  $\text{WO}_x$  thin films after EG treatment, and (c) comparison of w/ and w/o EG treated thin films of PEDOT:PSS,  $\text{WO}_x$  doped PEDOT:PSS and neat  $\text{WO}_x$  thin films.

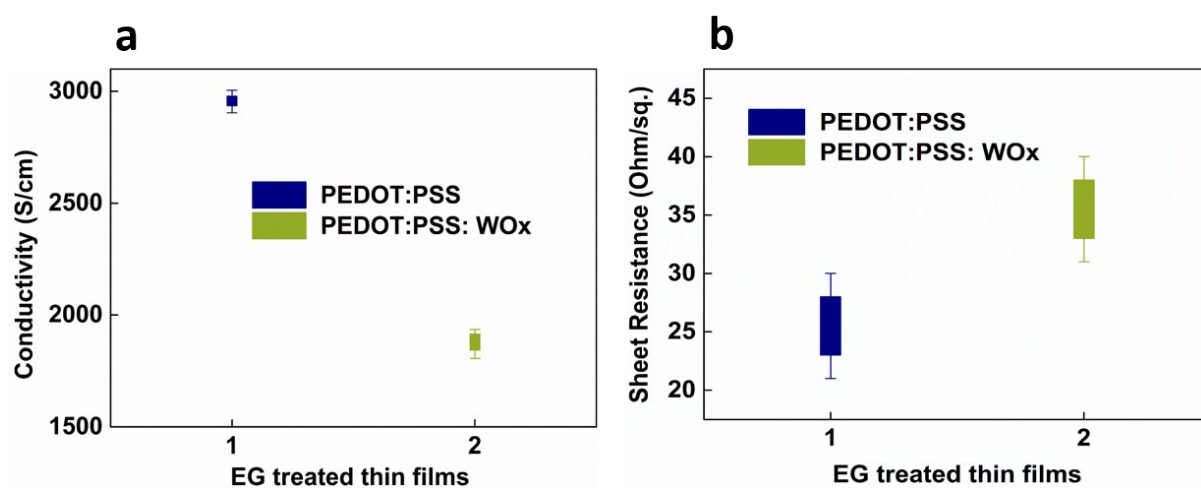


Figure S4. (a) Conductivity and (b) sheet resistance mean deviations of PEDOT:PSS/PEDOT:PSS: $\text{WO}_x$  of 10 samples. EG treatment carried out on each layers of multiple layered (180 nm thick 4 layers of PEDOT:PSS, and 160 nm thick 3 layers of PEDOT:PSS: $\text{WO}_x$ ).

1. Xia, K. Sun, J. Ouyang, *Adv. Mater.* 2012, 24, 2436.
2. N. Kim, H. Kang, J. H. Lee, S. Kee, S. H. Lee, and K. Lee, *Adv. Mater.* 2015, 27, 2317–2323.
3. W. Meng, R. Ge, Z. Li, J. Tong, T. Liu, Q. Zhao, S. Xiong, F. Jiang, L. Mao, Y. Zhou, *ACS Appl. Mater. Interfaces* 2015, 7, 14089–14094.
4. Y. H. Kim, C. Sachse, M. L. Machala, C. May, L. M. Meskamp, K. Leo, *Adv. Funct. Mater.* 2011, 21, 1076–1081.